NSN 5961-01-336-7779

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-336-7779 **Inclosure Material:** Ceramic or plastic **Overall Length:** 0.786 inches **Terminal Length:** 0.150 inches **Overall Height:** 0.400 inches **Overall Width:** Between 0.290 inches and 0.320 inches **End Application:** 5841-01-236-8951 detecting set, radar signals **Component Name And Quantity:** 6 transistor **Mounting Method: Terminal Features Provided:** Burn in and electrostatic sensitive **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 breakdown voltage, collector-to-emitter, base open all transistor and 60.0 collector to base voltage/static/emitter open all transistor and 5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 360.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Terminal Type And Quantity:** 14 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Fiig: A110a0

Yes - demil/mli